

isc Silicon PNP Darlington Power Transistor
2N6054
DESCRIPTION

- Built-in Base-Emitter Shunt Resistors
- Low Collector-Emitter Saturation Voltage
: $V_{CE(sat)} = -2.0V(\text{Max}) @ I_C = -4A$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = -80V(\text{Min})$
- Complement to type 2N6056
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

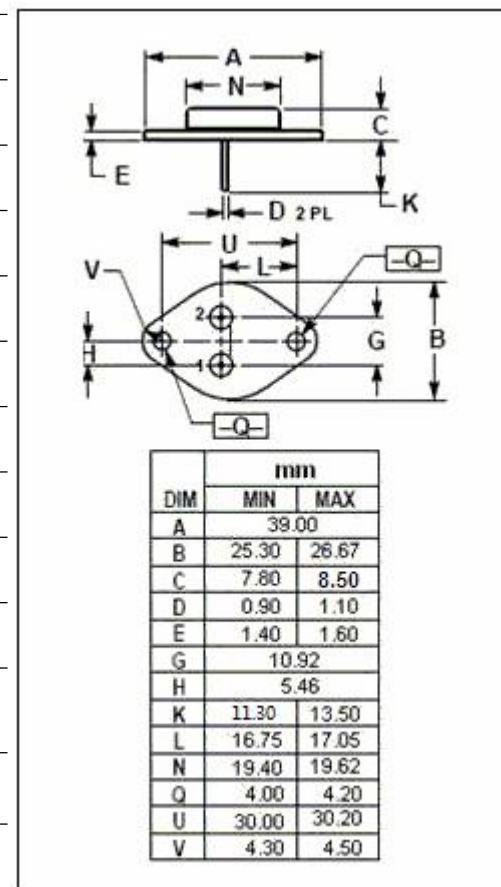
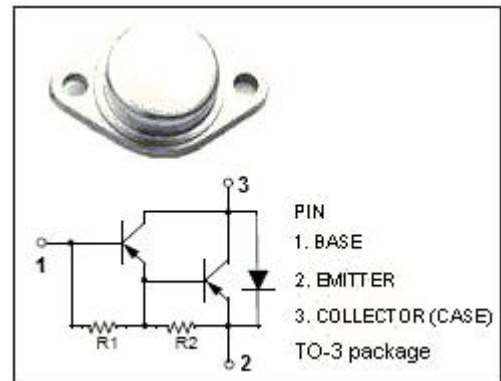
- Designed for general purpose amplifier and low frequency switching applications.

ABSOLUTE MAXIMUM RATINGS($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-8	A
I_{CM}	Collector Current-Peak	-16	A
I_B	Base Current	-120	mA
P_C	Collector Power Dissipation@ $T_C=25^\circ\text{C}$	100	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	ThermalResistance, Junction to Case	1.75	$^\circ\text{C}/\text{W}$



isc Silicon PNP Darlingtion Power Transistor**2N6054****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -50\text{mA}$; $I_B = 0$	-80		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -4\text{A}$; $I_B = -16\text{mA}$		-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -8\text{A}$; $I_B = -80\text{mA}$		-3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -8\text{A}$; $I_B = -80\text{mA}$		4.0	V
$V_{BE(on)}$	Base-Emitter On voltage	$I_C = -4\text{A}$; $V_{CE} = -3\text{V}$		-2.8	V
I_{CEO}	Collector Cutoff current	$V_{CE} = -40\text{V}$; $I_B = 0$		-0.5	mA
I_{CEX}	Collector Cutoff current	$V_{CE} = -80\text{V}$; $V_{BE(off)} = -1.5\text{V}$ $V_{CE} = -80\text{V}$; $V_{BE(off)} = -1.5\text{V}$, $T_C = 150^\circ\text{C}$		-0.5 -5.0	mA
I_{EBO}	Emitter Cut-off current	$V_{EB} = -5\text{V}$; $I_C = 0$		-2.0	mA
h_{FE-1}	DC Current Gain	$I_C = -4\text{A}$; $V_{CE} = -3\text{V}$	750	18000	
h_{FE-2}	DC Current Gain	$I_C = -8\text{A}$; $V_{CE} = -3\text{V}$	100		
C_{OB}	Output Capacitance	$I_E = 0$; $V_{CB} = -10\text{V}$; $f_{test} = 0.1\text{MHz}$		350	pF

Notice:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.